

Specification Amendments

Please replace the paragraph beginning on page 13, line 32, with the amended paragraph, as follows:

During the read function, the light emitters 43 emit a lower level energy field to locally excite charge carriers in the LASL 4732 of the diode 41, as discussed with respect to Figure 42. The amount of the beam that reaches the LASL 4732 will depend on the state of the storage area 45. Thus the storage layer acts primarily as a variable absorber or reflector of the beam during the read stage, depending on the state of the storage area. An additional field may be applied across interface 47 by a voltage source 48. The current that results from carriers passing across the diode interface between layer 47 and layer 44 can be monitored by a detection signal 49 taken across the interface between layer 47 and layer 44 to determine the state of data storage areas 45. Alternatively, the open circuit photo-voltage generated across diode 41 could be monitored.